



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
-60V	$28m\Omega$ @ $V_{GS} = -10V$	-7A		
-00 V	$35m\Omega$ @ $V_{GS} = -4.5V$	-6.2A		

Features and Benefits

- Low On-Resistance
- · Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

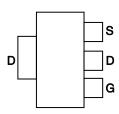
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.112 grams (Approximate)

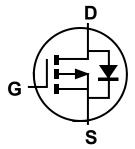




Top View



Pin Out - Top View



Equivalent Circuit

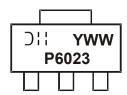
Ordering Information (Note 4)

Part Number Compliance		Case	Packaging	
DMP6023LE-13	Standard	SOT223	2,500/Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



O':: = Manufacturer's Marking P6023 = Marking Code YWW = Date Code Marking Y or Y = Year (ex: 4 = 2014) WW = Week (01 - 53)



Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	-60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Prais Current (Note E) V = 10V	T _A = +25°C T _A = +70°C	I _D	-7 -5.6	А
Continuous Drain Current (Note 5) V _{GS} = -10V	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	I _D	-18.2 -14.5	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-50	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	-2	Α	
Avalanche Current, L = 0.1mH		I _{AS}	-35.5	А
Avalanche Energy, L = 0.1mH		Eas	62.9	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	P_{D}	2 1.3	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	60	°C/W
Total Power Dissipation (Note 5) $T_C = +25^{\circ}C$		P _D	17.3	W
Thermal Resistance, Junction to Case (Note 5)		$R_{ heta JC}$	7.2	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage		-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C		_	_	-1	μA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage		_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	D	_	_	28	mΩ	V _{GS} = -10V, I _D = -5A
Static Dialit-Source Off-Resistance	R _{DS(ON)}	_	_	35		$V_{GS} = -4.5V$, $I_{D} = -4A$
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	_	2569	_	pF	V 20V V 20V
Output Capacitance	Coss	_	179	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1MHz
Reverse Transfer Capacitance	C _{rss}	_	143	_	pF	- I - IIVIHZ
Gate Resistance	R_g	_	8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	26.5	_	nC	
Total Gate Charge (V _{GS} = -10V)		_	53.1	_	nC	
Gate-Source Charge	Q _{gs}	_	7.1	_	nC	$V_{DS} = -30V, I_{D} = -5A$
Gate-Drain Charge	Q_{gd}	_	12.6	_	nC	
Turn-On Delay Time	t _{D(on)}		6	_	ns	
Turn-On Rise Time	t _r		7.1	_	ns	V _{GS} = -10V, V _{DS} = -30V,
Turn-Off Delay Time	t _{D(off)}		110	_	ns	$R_G = 3\Omega, I_D = -5A$
Turn-Off Fall Time	t _f		62	_	ns	1
Body Diode Reverse Recovery Time	t _{rr}		20	_	nS	L 5A 31/34 400A/
Body Diode Reverse Recovery Charge	Qrr	-	14	_	nC	I _F = -5A, di/dt = 100A/μs

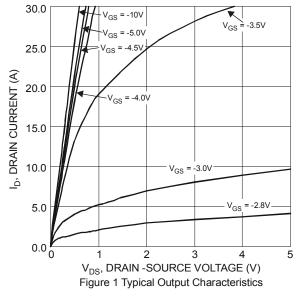
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square pad layout.

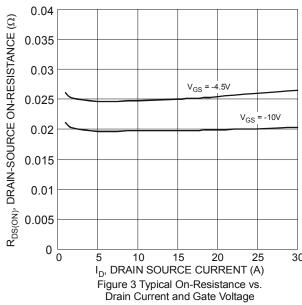
^{6.} Short duration pulse test used to minimize self-heating effect.

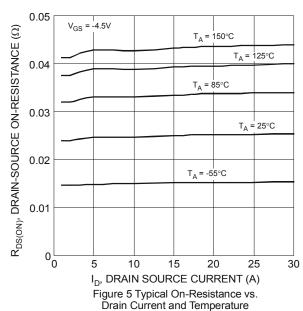
^{7.} Guaranteed by design. Not subject to product testing.

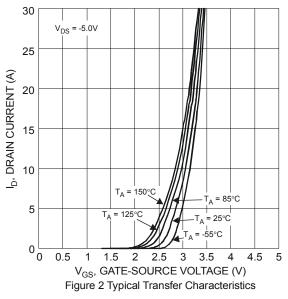


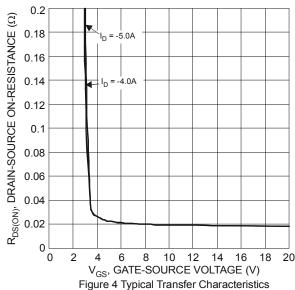












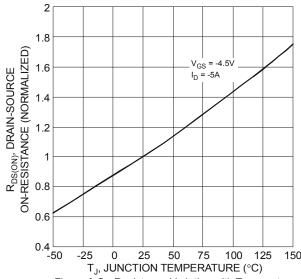
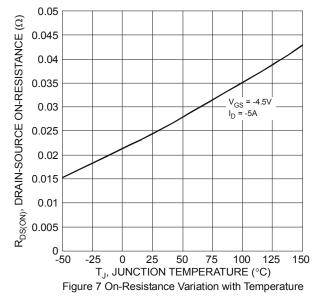
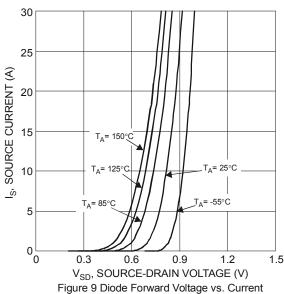
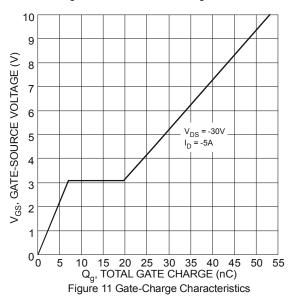


Figure 6 On-Resistance Variation with Temperature









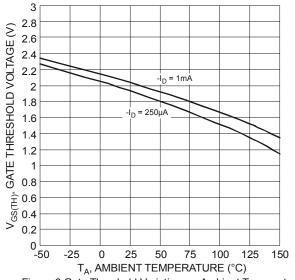
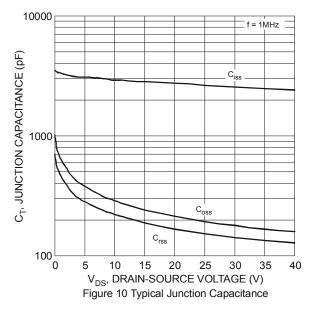
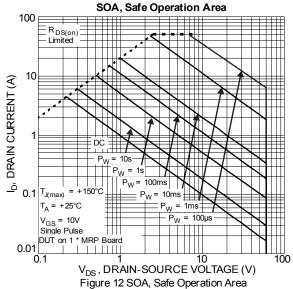


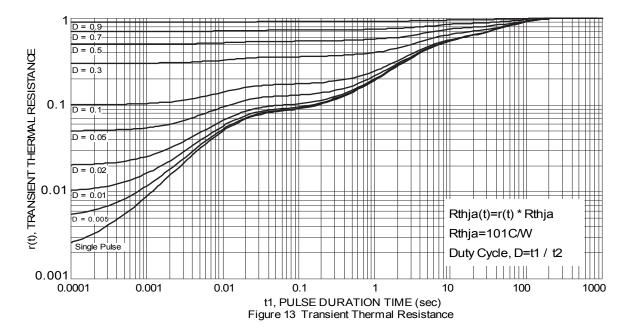
Figure 8 Gate Threshold Variation vs. Ambient Temperature





January 2015

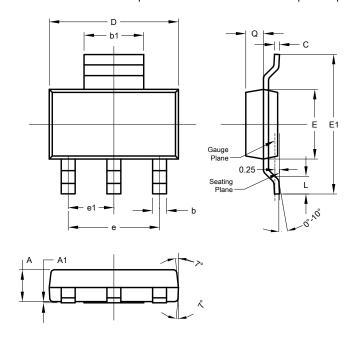






Package Outline Dimensions

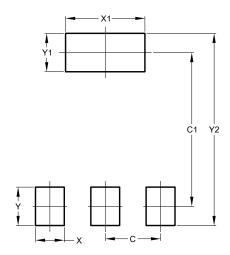
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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